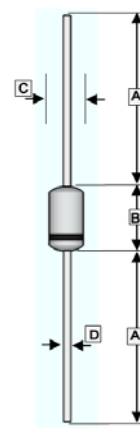


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

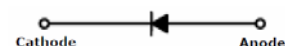
FEATURES

- Fast Switching Device (TRR <4.0 nS)
- DO-34 Package (JEDEC DO-204)
- Through-Hole Device Type Mounting
- Hermetically Sealed Glass
- Compression Bonded Construction
- Solder Hot Dip Tin (Sn) Terminal Finish
- Cathode Indicated By Polarity Band

DO-34



REF.	Millimeter	
	Min.	Max.
A	25.0	38.1
B	2.16	3.04
C	1.27	1.9
D	0.46	0.56



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Working Inverse Voltage	W _{IV}	90	V
Average Rectified Current	I _O	150	mA
Non-repetitive Peak Forward Current	I _{FM}	450	mA
Peak Forward Surge Current (Pulse Width = 1.0 µsecond)	I _{FM(Surge)}	2	A
Power Dissipation	P _D	300	mW
Junction, Storage Temperature	T _J , T _{STG}	150, -65~150	°C

Note:

1. These ratings are limiting values above which the serviceability of the diode may be impaired.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Max.	Unit	Test Condition
Breakdown Voltage	B _V	80	-	V	I _R =500nA
Leakage Current	I _R	-	500	nA	V _R =80V
Forward Voltage	V _F	-	1.2	V	I _F =100mA
Capacitance	C	-	4	pF	V _R =0, f=1MHz
Reverse Recovery Time	T _{RR}	-	4	nS	I _F =I _R =10mA, I _{RR} =1mA, R _L =100Ω

CHARACTERISTIC CURVE

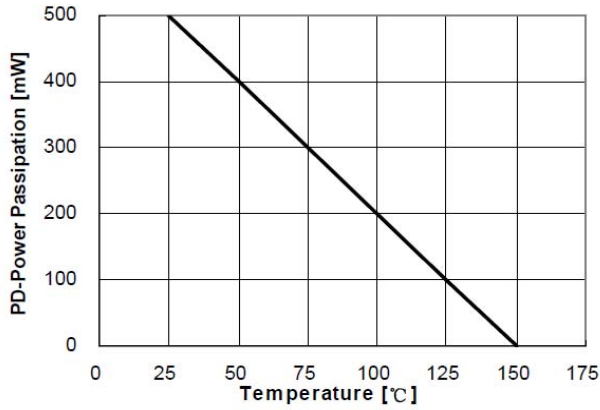


Figure 1. Power Dissipation vs Ambient Temperature

Valid provided leads at a distance of 0.8mm from case are kept at

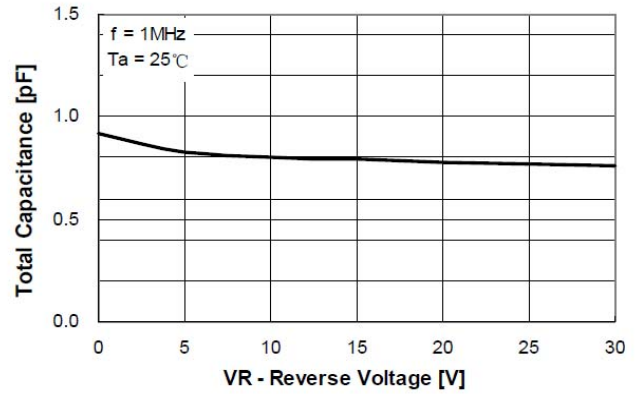


Figure 2. Total Capacitance

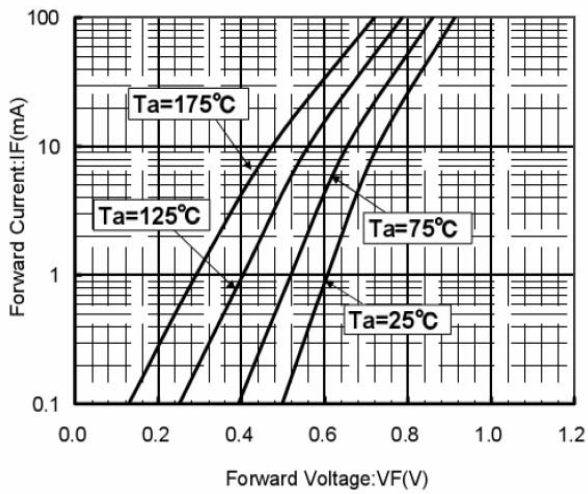


Figure 3.VF—IF Characteristics

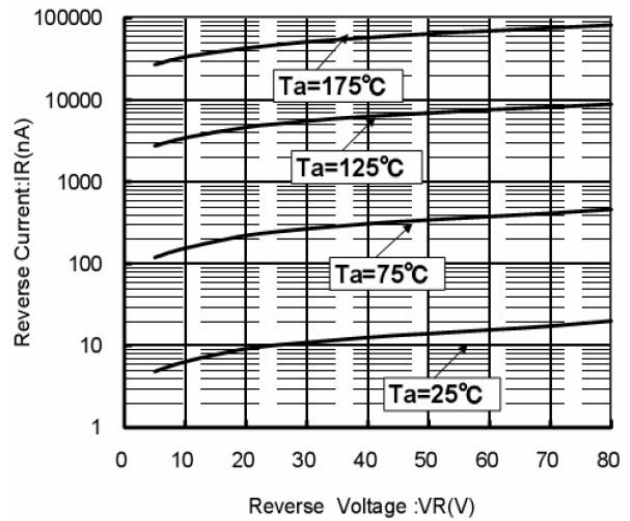


Figure 4.VR—IR Characteristics